

L15 ANSWER 4 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN
 AN 2001:718959 HCAPLUS
 DN 135:264923
 TI Low-pressure CVD apparatus
 IN Loan, James F.; Salerno, Jack P.
 PA Cvd Systems, Inc., USA
 SO U.S., 64 pp., Cont.-in-part of U.S. Ser. No. 291.871.
 CODEN: USXXAM

DT Patent
 LA English
 IC ICM C23C014-26
 NCL 118726000
 CC 75-1 (Crystallography and Liquid Crystals)
 FAN.CNT 4

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 6296711	B1	20011002	US 1999-421823	19991020
	US 2001016364	A1	20010823	US 1999-291871	19990414
	WO 2001029282	A2	20010426	WO 2000-US28998	20001020
	WO 2001029282	A3	20011122		
	US 2002076492	A1	20020620	US 2001-850454	20010507

PRAI US 1998-60007 A2 19980414
 US 1999-291871 A2 19990414
 US 1999-421823 A2 19991020
 US 1999-421828 A2 19991020
 US 2000-678460 A2 20001003

AB An app. for CVD includes a dispenser for dispensing a precursor to a vaporizer positioned within a vaporization chamber. A delivery conduit joins the vaporization with a process chamber. A flow meter is positioned within the delivery conduit for measuring the flow of precursor through the delivery conduit. A flow controller is likewise positioned within the delivery conduit for controlling the flow of precursor in response to the measured flow rate.

RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
 (low-pressure CVD app.)

RN 172901-22-3 HCAPLUS
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-,
 (OC-6-23) - (9CI) (CA INDEX NAME)

